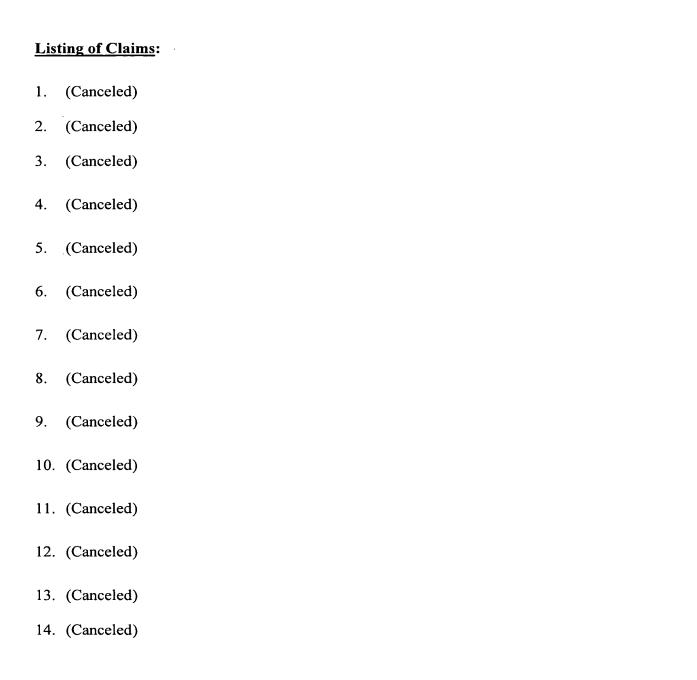
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Docket No.: 8733.1038.00-US

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.



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15. (Currently Amended) A method of fabricating an IPS mode LCD, comprising:

forming a gate line and a data line on a first substrate;

forming a thin film transistor at a crossing point of the gate line and the data line;

forming a pixel electrode and a common electrode on [[a]] the first substrate;

forming a passivation film on the pixel electrode and the common electrode; [[and]]

performing an orientation treatment of the passivation film by irradiating an ion beam on the passivation film;

forming a black matrix layer on a second substrate;

forming a color filter layer on the black matrix layer;

forming an overcoat layer on the color filter layer; and

performing an orientation treatment of the overcoat layer by irradiating an ion beam on the passivation film,

wherein the pixel electrode, the common electrode and the gate line are arranged in a zigzag configuration,

wherein irradiating the ion beam comprises: generating a plasma from an ion beam source, forming an ion beam from the plasma, accelerating the ion beam by applying an electric field to an ion beam acceleration medium; and irradiating the ion beam on one of the first and second substrates at a predetermined angle.

- 16. (Original) The method according to claim 15, further comprising forming a liquid crystal layer between the first and second substrates.
- 17. (Original) The method according to claim 16, wherein forming a liquid crystal layer includes injecting the liquid crystal into a space between the first and second substrates.
- 18. (Original) The method according to claim 16, wherein forming a liquid crystal layer includes dispensing a liquid crystal on at least one of the first and second substrates.
- 19. (Original) The method according to claim 15, wherein the passivation film and the overcoat layer include one of an organic material and an inorganic material.

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20. (Original) The method according to claim 19, wherein the passivation film and the overcoat layer are formed of one of a photo-acryl, a BCB (benzo cyclobutine), and a silicon oxide (SiOx) and a silicon nitride (SiNx).

- 21. (Canceled).
- 22. (Canceled).
- 23. (Canceled).
- 24. (Canceled).

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